



N-Channel and N-Channel Complementary MOSFET



Product Summary

- V_{DS} 40V
- I_D 70A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 5.3m Ω
- 100% EAS Tested
- 100% V_{DS} Tested

General Description

- Excell] a a =25 $\ddot{N}$ unless otherwise noted)

Parameter			Symbol	Limit	Unit
Drain-source Voltage			V _{DS}	40	V
Gate-source Voltage			V _{GS}	±20	V
Continuous Drain Current (Note 1,2)	Steady-State	T _A =25 -	I _D	16	A
		T _A =100 -		11	
Continuous Drain Current (Note 1,3)	Steady-State	T _C =25 -		70	
		T _C =100 -		49	
Pulsed Drain Current	T _C =25 , t _v ≤100μs		I _{DM}	250	A
Avalanche energy	V _G =10V, R _G =25Ω, L=0.5mH, I _{AS} =14A		EAS	49	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T _A =25 -	P _D	2.5	W
		T _A =100 -		1.25	
Total Power Dissipation (Note 1,3)	Steady-State	T _C =25 -		50	
		T _C =100 -		25	
Junction and Storage Temperature Range			T _J ,T _{STG}	-55 +175	-

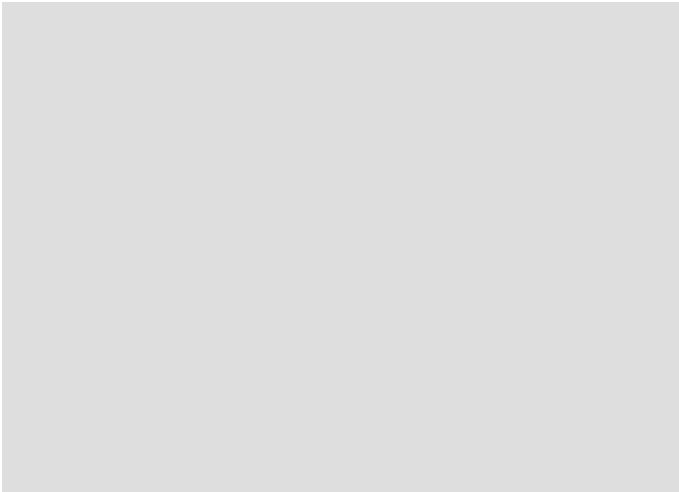
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	50	60	- /W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	2.5	3	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJGD5D3G04HQ	F1	YJGD5D3G04H	5000	10000	100000	13" reel



■ Typical Electrical and Thermal Characteristics Diagrams





YJGD5D3G04HQ

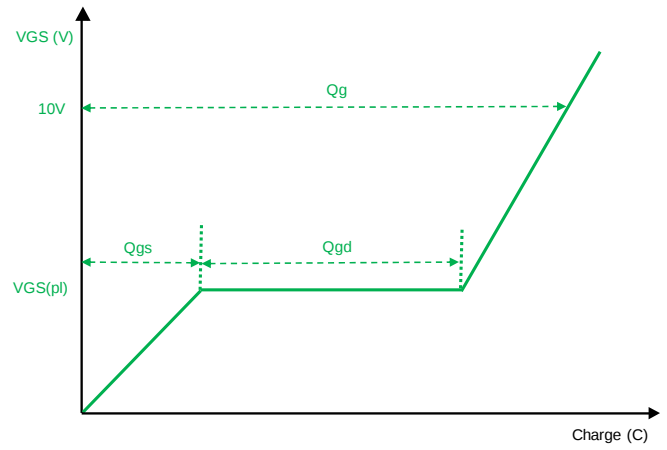
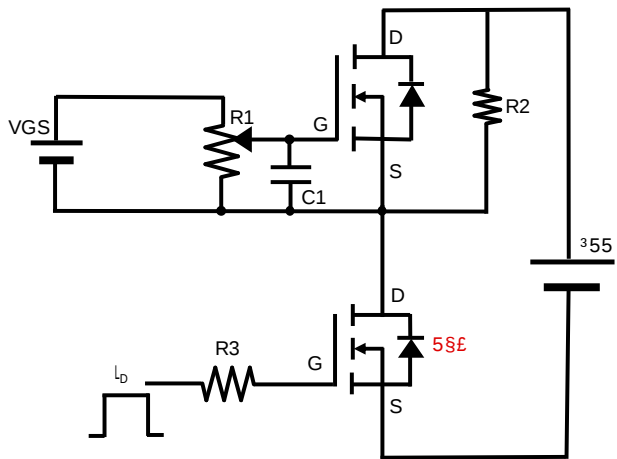
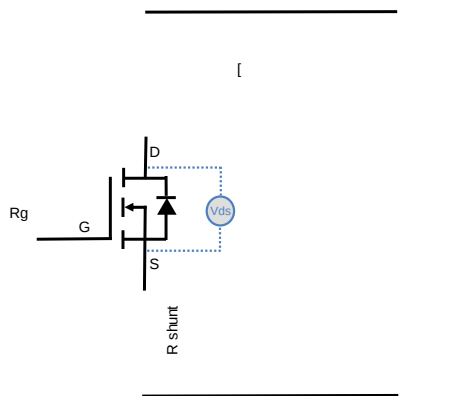


Figure B. Gate Charge Test Circuit & Waveform





YJGD5D3G04HQ

■ PDFN5060-8L-E-1.1mm Package information

